Doc No. TT4-EA-12308

Revision. 2

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MOS FET

MTM861280LBF

Panasonic

MTM861280LBF Silicon P-channel MOSFET

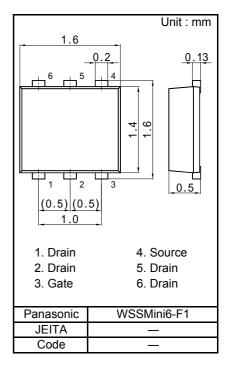
For Switching

■ Features

- Low drain-source On-state Resistance
 : RDS(on) typ. = 300 mΩ (VGS = -4.0 V)
- Halogen-free / RoHS compliant (EU RoHS / UL-94 V-0 / MSL : Level 1 compliant)
- Marking Symbol : ML

■ Packaging

Embossed type (Thermo-compression sealing): 10 000 pcs / reel (standard)



■ Absolute Maximum Ratings Ta = 25 °C

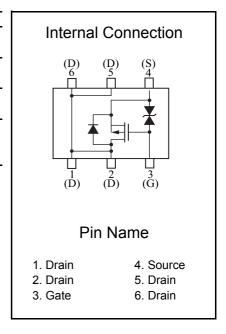
Parameter	Symbol	Rating	Unit
Drain to Source Voltage	VDS	-20	V
Gate to Source Voltage	VGS	±12	V
Drain Current	ID	-1.0	А
Drain Current (Pulsed) *1	IDp	-4.0	
Total Power Dissipation	PD1 *2	540	mW
	PD2 *3	150	IIIVV
Channel Temperature	Tch	150	
Operating Ambient Temperature	Topr	-40 to +85	°C
Storage Temperature Range	Tstg	-55 to +150	

- Note) *1 $t \le 10 \mu s$, Duty cycle $\le 1 \%$
 - *2 Glass epoxy substrate (25.4 \times 25.4 \times t 0.8 mm) coated with copper foil (more than 300 mm 2)
 - *3 Non-heat sink

Established: 2010-02-04

: 2013-10-17

Revised



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■ Electrical Characteristics Ta = 25 °C ± 3 °C

Parameter	Symbol	Conditions	Min	Тур	Max	Unit
Drain-source Breakdown Voltage	VDSS	ID = -1.0 mA, VGS = 0 V	-20			V
Zero Gate Voltage Drain Current	IDSS	VDS = -20 V, VGS = 0 V			-1.0	μА
Gate-source Leakage Current	IGSS	VGS = ±10 V, VDS = 0 V			±10	μА
Gate-source Threshold Voltage	Vth	ID = -1.0 mA, VDS = -10 V	-0.45	-1.0	-1.5	V
Drain-source On-state Resistance *1	RDS(on)1	ID = -0.5 A, VGS = -4.0 V		300	420	mΩ
	RDS(on)2	ID = -0.5 A, VGS = -2.5 V		420	560	
Forward transfer admittance *1	Yfs	ID = -0.5 A, VDS = -10 V	1.0	2.0		S
Input Capacitance	Ciss	VDS = -10 V, VGS = 0 V		80		pF
Output Capacitance	Coss	f = 1 MHz		12		
Reverse Transfer Capacitance	Crss	1 - 1 1011 12		12		
Turn-on Delay Time *2	td(on)	VDD = -15 V, VGS = 0 to -4 V		12		ns
Rise Time *2	tr	ID = -0.5 A		6		
Turn-off Delay Time *2	td(off)	VDD = -15 V, VGS = -4 to 0 V		17		ns
Fall Time *2	tf	ID = -0.5 A		10		

Note) Measuring methods are based on JAPANESE INDUSTRIAL STANDARD JIS C 7030 Measuring methods for transistors.

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Established: 2010-02-04 : 2013-10-17 Revised

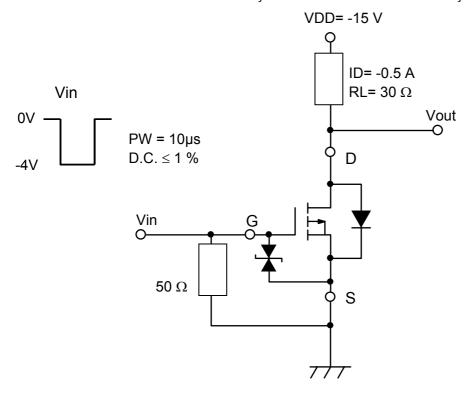
^{*2} Measurement circuit for Turn-on Delay Time / Rise Time / Turn-off Delay Time / Fall Time

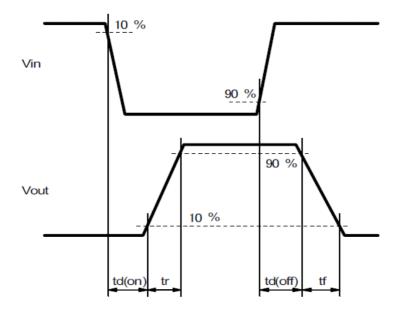
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*2 Measurement circuit for Turn-on Delay Time / Rise Time / Turn-off Delay Time / Fall Time





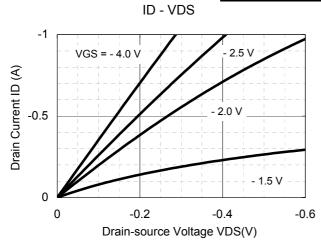
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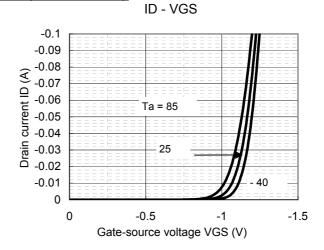
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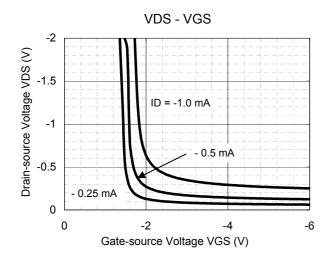
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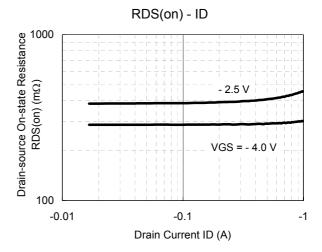
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Technical Data (reference)

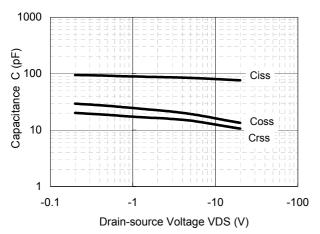








Capacitance - VDS

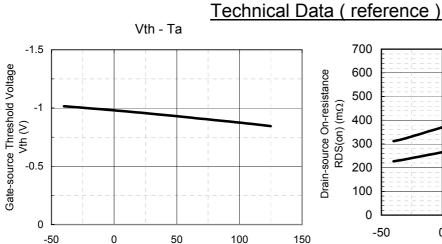


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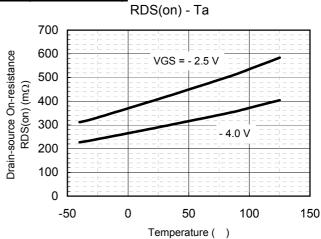
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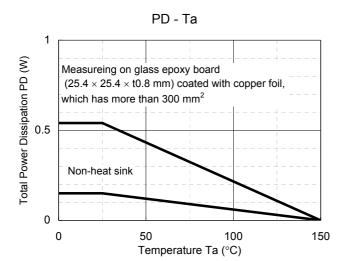
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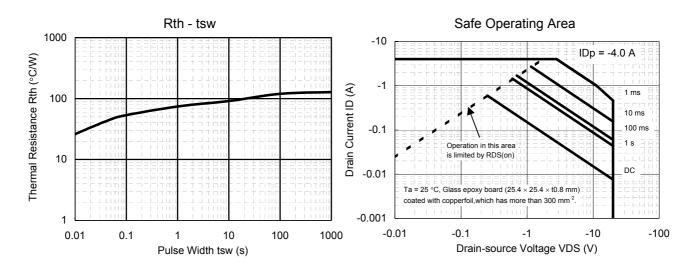
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Temperature ()







Revision. 2

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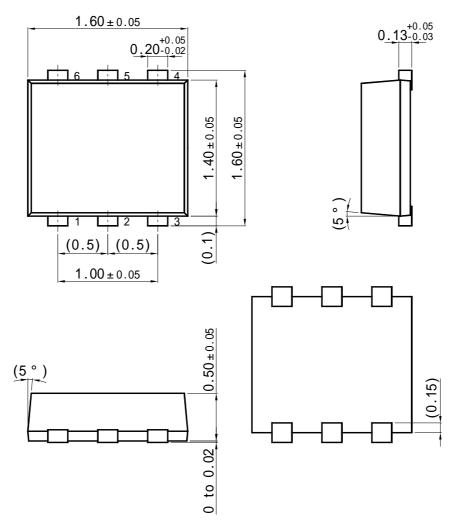
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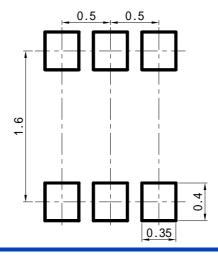
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WSSMini6-F1

Unit: mm



■ Land Pattern (Reference) (Unit: mm)



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